

## 2024년 1월 24일(수)-26일(금) | 경주화백컨벤션센터(HICO)

2024년 1월 26일(금), 13:45-15:30 Room I(203),2층

## D. Thin Film Process Technology 분과

## [FI2-D] Atomic Layer Deposition - II

#### 좌장: 김성근 책임(한국과학기술연구원), 최병준 교수(서울과학기술대학교)

| FI2-D-1<br>13:45-14:00 | Modulation of Atomic Layer Deposition for Improvement of<br>Conformality on High Aspect Ratio Substrates<br>Jiwon Kim <sup>1</sup> , Changbong Yeon <sup>2</sup> , Deok-Hyeon Cho <sup>2</sup> , Jaesun Jung <sup>2</sup> , and Bonggeun<br>Shong <sup>1</sup><br><sup>1</sup> Hongik University, <sup>2</sup> Soulbrain  |
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| FI2-D-2<br>14:00-14:15 | Theoretical Screening of Tungsten Precursors toward Inherent Area-<br>selective Atomic Layer Deposition of WO <sub>3</sub> between Nitride Substrates<br>Su-Jin Kwon, Junhui Choi, Ju Hyeon Jung, and Bonggeun Shong<br>Chemical Engineering, Hongik University   |
| FI2-D-3<br>14:15-14:30 | Enhanced Deposition Selectivity of High-k Dielectrics by Vapor-Dosed<br>Self-Assembled Monolayer Inhibitors Combined with Selective Lift-Off<br>Jeong-Min Lee and Woo-Hee Kim<br>Department of Materials Science and Chemical Engineering, Hanyang University   |
| FI2-D-4<br>14:30-14:45 | Theoretical Analysis on the Influence of Ge Precursors toward Atomic<br>Layer Deposition of Germanium Tellurides<br>Hyeon Cho and Bonggeun Shong<br>Hongik University   |
| FI2-D-5<br>14:45-15:00 | Growth Characteristics of Plasma-Enhanced Atomic Layer Deposition<br>of SiN <sub>x</sub> by BTBAS and BDEAS with a Very High Frequency Plasma<br>Source<br>Young-Jin Lim <sup>1</sup> , Min-Jeong Rhee <sup>1</sup> , Ngoc Le Trinh <sup>2</sup> , Han-Bo-Ram Lee <sup>2</sup> , and II-Kwon<br>Oh <sup>1</sup><br><sup>1</sup> Department of Intelligence Semiconductor Engineering, Ajou University,<br><sup>2</sup> Department of Materials Science and Engineering, Incheon National University |
| FI2-D-6<br>15:00-15:15 | Temperature-dependentSurfaceReactionsinAtomicLayerDeposition of Titanium NitrideJae Min Jang, Ju Hyeon Jung, and Bonggeun ShongHongik University  |

# 제 31회 한국반도체학술대회 The 31st Korean Conference on Semiconductors

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|             | Theoretical Analysis of Niobium Precursors toward Inherent Area- |
|-------------|--|
| FI2-D-7     | selective Atomic Layer Deposition between Nitride Substrates     |
| 15:15-15:30 | Junhui Choi, Miso Kim, and Bonggeun Shong                        |
|             | Hongik University  |